Feature

- Precision MEMS process
- High performance, shielded, Micro-cavity structure
- Silicon substrate, 50Ω CPW output
- Au wire bonding, for MCM applications

Environmental Specifications

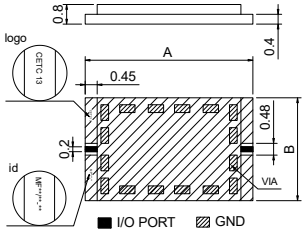
Operating Temperature	-55℃~+85℃
Storage Temperature	-55℃~+125℃
Max. Input Power	35dBm

Electrical Specifications(T_A=+25℃)

Parameter	Min.	Typ.	Max.	Unit
Center Freq. (f_0)	-	9.95	-	GHz
Pass Band	9.4	-	10.5	GHz
Ripple in Pass band	-	-	1	dB
Insertion Loss @ f_0	-	-	1.5	dB
Return Loss	12	-	-	dB
Out of band Attenuation	≥30@8.7GHz&11.3GHz			dB
	≥40@8.5GHz&11.4GHz			dB
	≥60@DC~7GHz			dB
	≥50@12~16GHz			dB
Group Delay Variation	≤1@9.4~10.5GHz			ns
Linear Phase	≤±4@9.4~10.5GHz			°

S2P file name: SiMF9R9_1R1-6E3.s2p

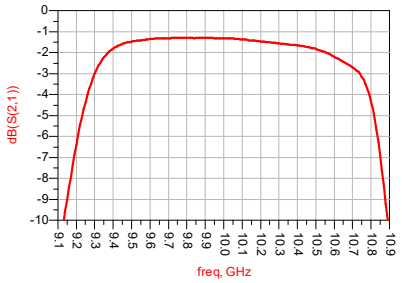
Outline Drawing



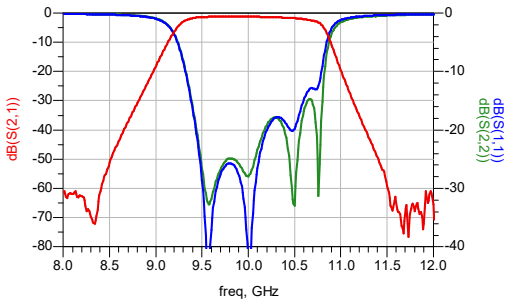
Symbol	Value (mm)		
	Min.	Nominal	Max.
A	6.4	-	6.5
B	3.9	-	4.0

Typical Test Curves

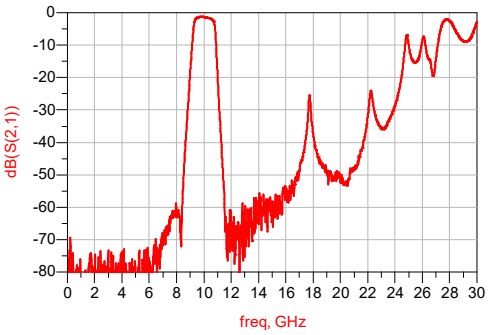
Insertion Loss VS Frequency (T_A=25℃)



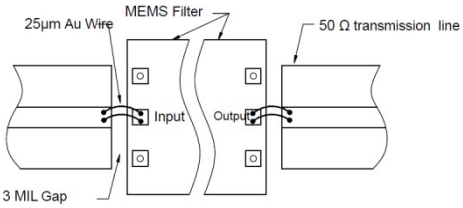
Insertion Loss & Return Loss VS Frequency (T_A=25℃)



Broadband Insertion Loss VS Frequency (T_A=25℃)



Recommended Assembly Diagrams



Application Notes:

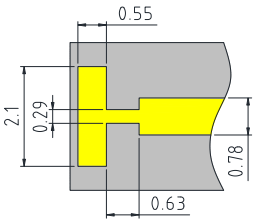
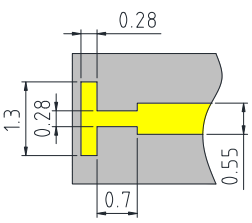
1. The chip is back-metalized and can be die mounted with AuSn eutectic performs or with electrically conductive epoxy (for example ME8456).

2. The die should be assembled on carriers like Kovar or Mu-Cu which have same Coefficient of thermal expansion. (2.9ppm/℃) with Silicon, thickness 0.2mm max.

3. Handle the chips in a clean environment. DO NOT attempt to clean the chip using liquid cleaning systems.

4. Handle the chip along the edges with a vacuum collet or with a sharp pair of bent tweezers.

5. Recommended to use T structure as below for bonding.

Rogers 5880, 10mil	Rogers 4350, 10mil
	

6. If you have any questions, please contact us.